

HAT1108C

Silicon P Channel MOS FET
Power Switching

REJ03G1234-0500

Rev.5.00

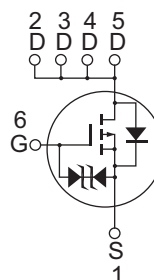
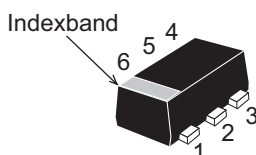
Aug 30, 2006

Features

- Low on-resistance
 $R_{DS(on)} = 155 \text{ m}\Omega$ typ. (at $V_{GS} = -10 \text{ V}$)
- Low drive current.
- 4.5 V gate drive devices.
- High density mounting

Outline

RENESAS Package code: PWSF0006JA-A
(Package name: CMFPAK-6)



1. Source
2. Drain
3. Drain
4. Drain
5. Drain
6. Gate

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source voltage	V_{DSS}	-30	V
Gate to Source voltage	V_{GSS}	-20 / +10	V
Drain current	I_D	-1.5	A
Drain peak current	I_D (pulse) ^{Note 1}	-6	A
Body - Drain diode reverse drain current	I_{DR}	-1.5	A
Channel dissipation	P_{ch} ^{Note 2}	830	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$

2. When using the glass epoxy board. (FR4 $40 \times 40 \times 1.6\text{mm}$), $T_a = 25^\circ\text{C}$

Electrical Characteristics

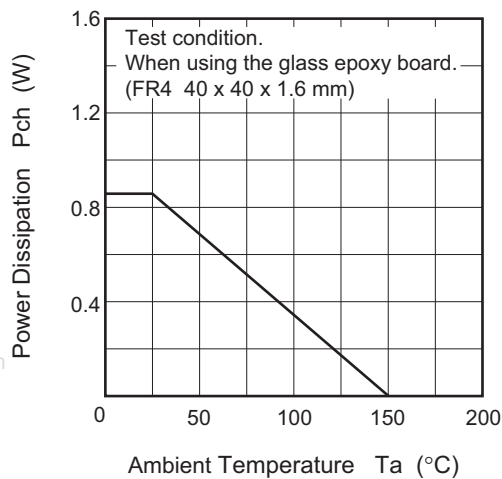
(Ta = 25°C)

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to Source breakdown voltage	$V_{(BR)GSS}$	-20 +10	—	—	V	$I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0$
Gate to Source leakage current	I_{GSS}	—	—	± 10	μA	$V_{GS} = -16/ +8 \text{ V}$, $V_{DS} = 0$
Drain to Source leakage current	I_{DSS}	—	—	-1	μA	$V_{DS} = -30 \text{ V}$, $V_{GS} = 0$
Gate to Source cutoff voltage	$V_{GS(th)}$	-0.5	—	-2.0	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$ ^{Note4}
Drain to Source on state resistance	$R_{DS(on)}$	—	155	194	$\text{m}\Omega$	$I_D = -0.75\text{A}$, $V_{GS} = -10 \text{ V}$ ^{Note4}
		—	245	356	$\text{m}\Omega$	$I_D = -0.75\text{A}$, $V_{GS} = -4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	0.65	1	—	S	$I_D = -0.75\text{A}$, $V_{DS} = -10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	160	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	50	—	pF	
Reverse transfer capacitance	C_{rss}	—	30	—	pF	
Total gate charge	Q_g	—	3	—	nC	$V_{DS} = -10 \text{ V}$, $V_{GS} = -10 \text{ V}$, $I_D = -1.5 \text{ A}$
Gate to Source charge	Q_{gs}	—	0.2	—	nC	
Gate to Drain charge	Q_{gd}	—	0.6	—	nC	
Turn - on delay time	$t_{d(on)}$	—	20	—	ns	$V_{DS} = -10 \text{ V}$, $V_{GS} = -10 \text{ V}$, $I_D = -0.75 \text{ A}$, $R_L = 13.3 \Omega$, $R_g = 4.7 \Omega$
Rise time	t_r	—	13	—	ns	
Turn - off delay time	$t_{d(off)}$	—	28	—	ns	
Fall time	t_f	—	5	—	ns	
Body - Drain diode forward voltage	V_{DF}	—	-0.85	-1.2	V	$I_F = -1.5 \text{ A}$, $V_{GS} = 0$

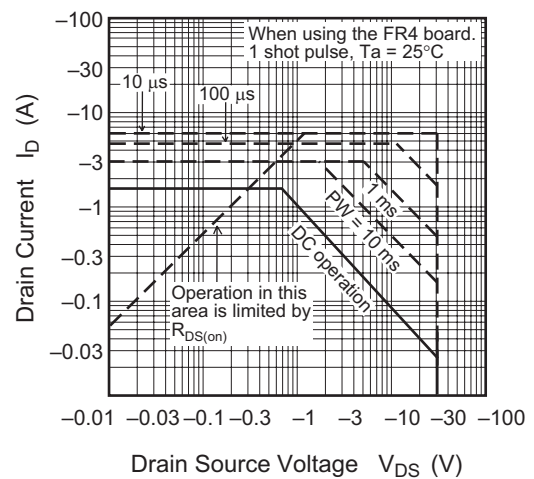
Notes: 4. Pulse test

Main Characteristics

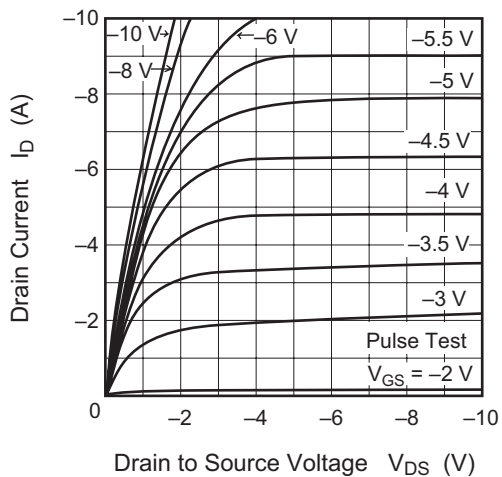
Power vs. Temperature Derating



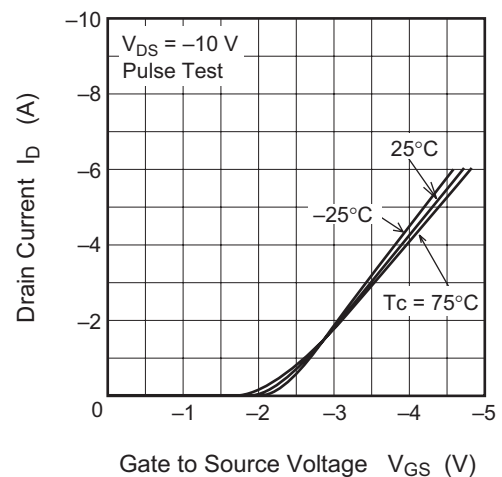
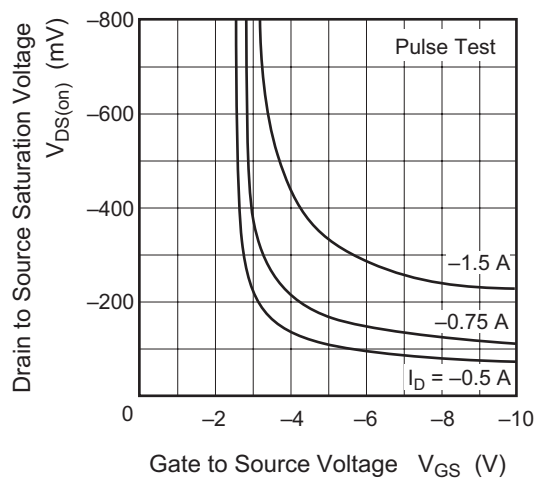
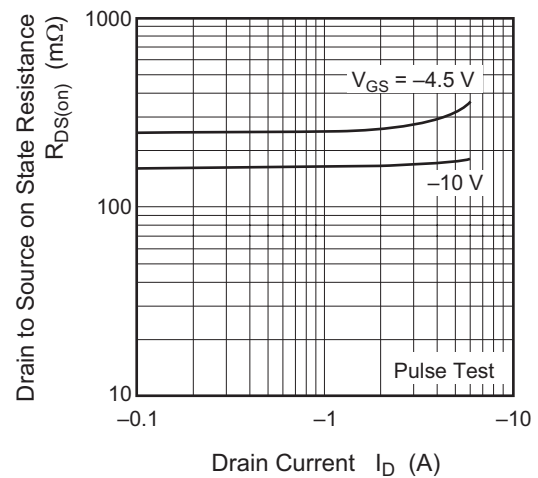
Maximum Safe Operation Area



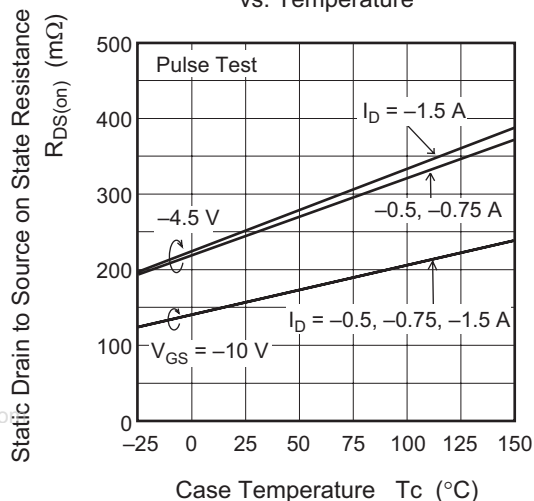
Typical Output Characteristics



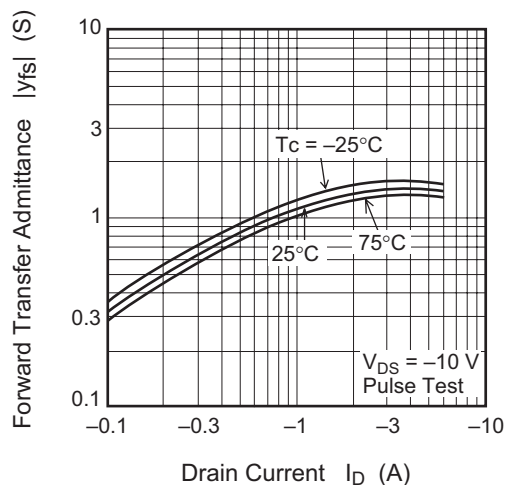
Typical Transfer Characteristics

Drain to Source Saturation Voltage vs.
Gate to Source VoltageStatic Drain to Source on State Resistance
vs. Drain Current

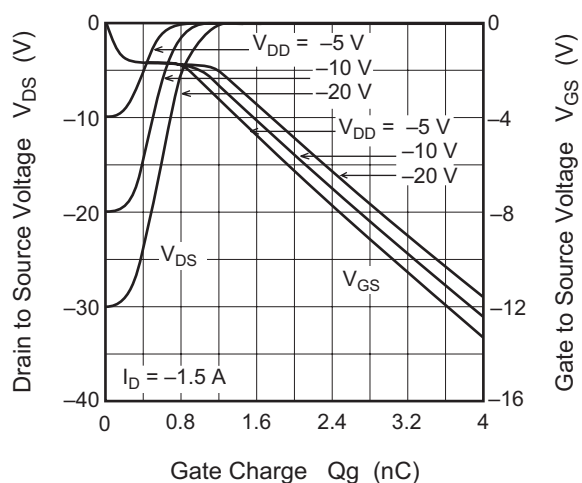
Static Drain to Source on State Resistance vs. Temperature



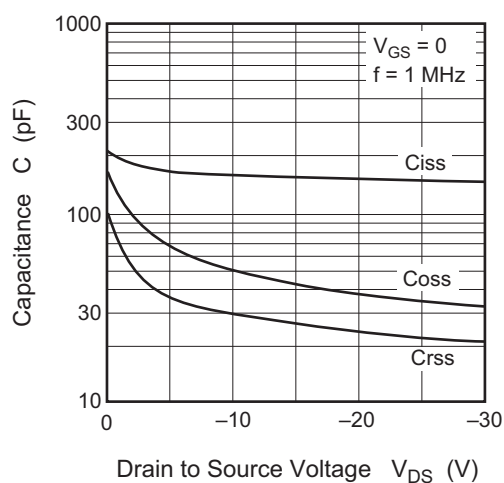
Forward Transfer Admittance vs. Drain Current



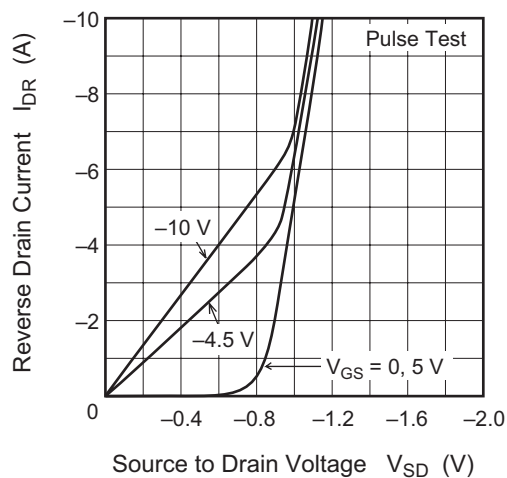
Dynamic Input Characteristics



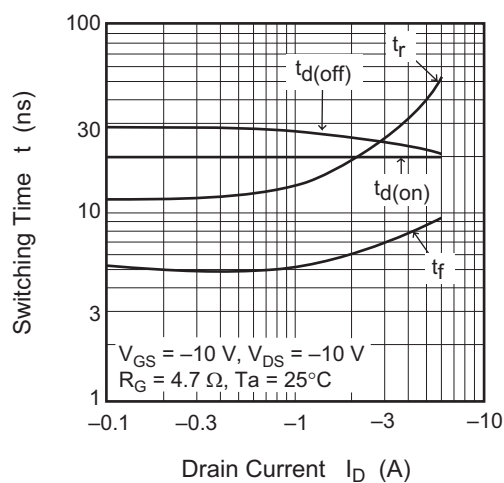
Typical Capacitance vs. Drain to Source Voltage

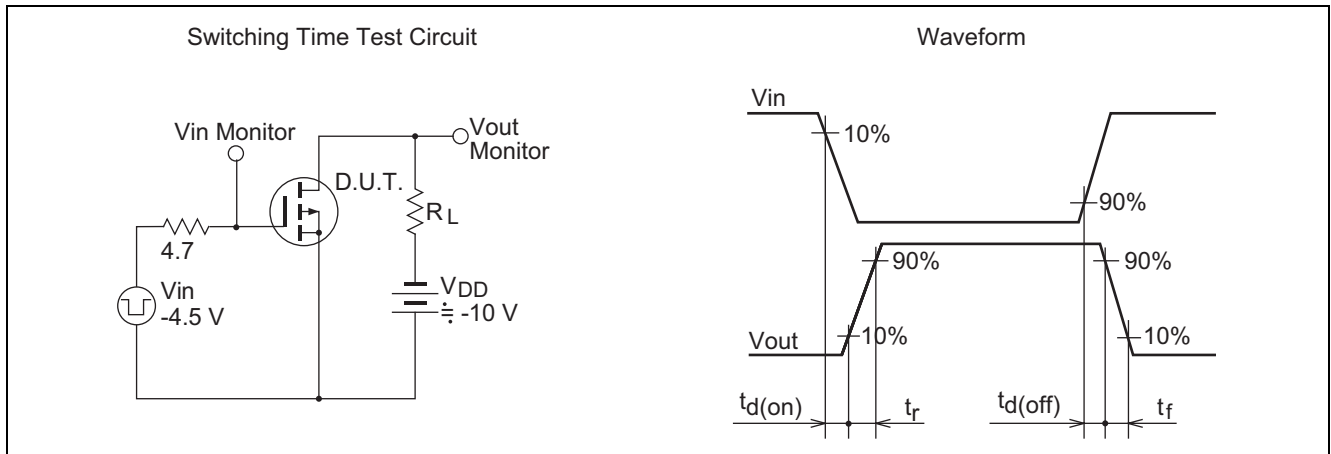


Reverse Drain Current vs. Source to Drain Voltage



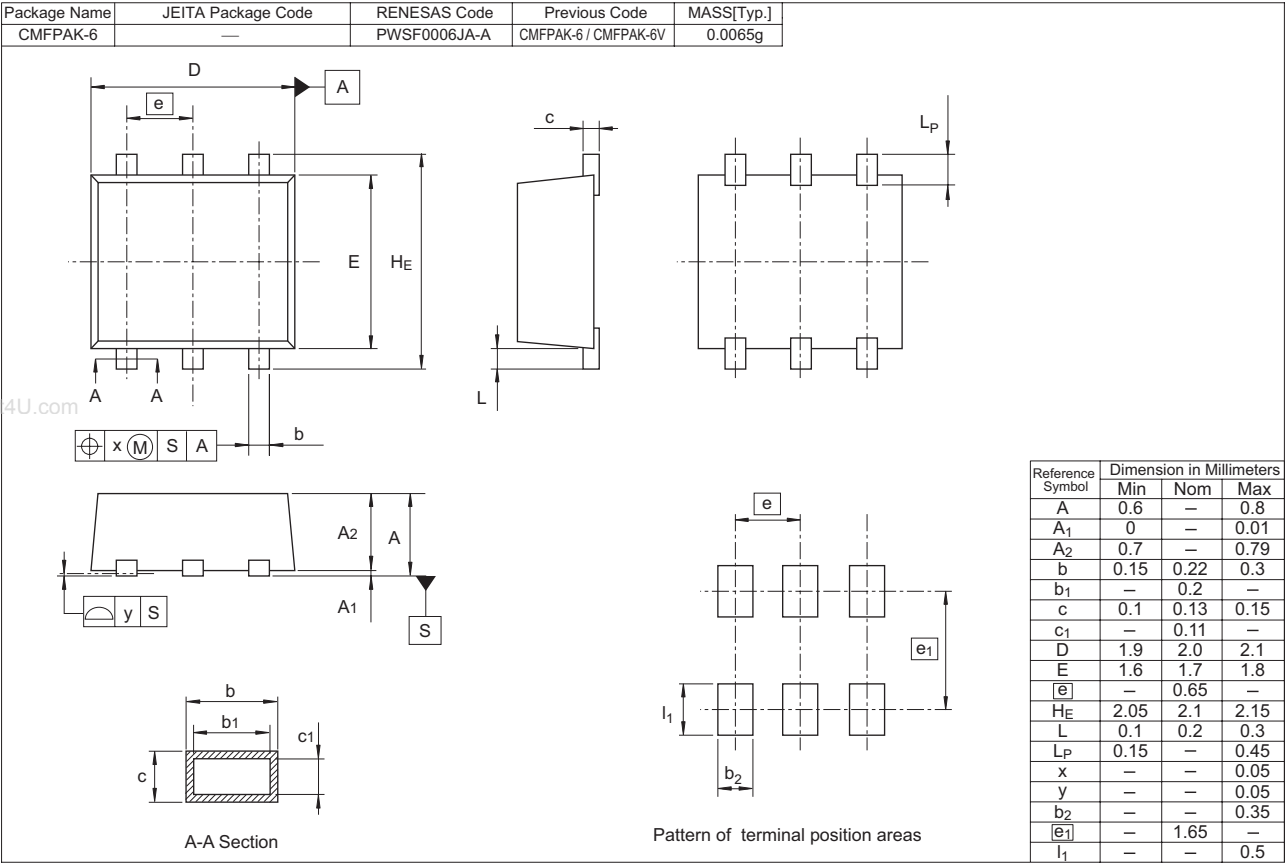
Switching Characteristics





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Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT1108C-EL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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